

Abstract

**Method and apparatus for the treatment of a
semiconductor wafer**

The invention relates to a method for the treatment of a semiconductor wafer, comprising the following steps:

a) position-dependent measurement of a parameter which characterizes the semiconductor wafer in order to determine the position-dependent value of said parameter over an entire surface of the semiconductor wafer,

b) oxidation of said entire surface of the semiconductor wafer under the action of an oxidizing agent and simultaneous exposure of said entire surface, the oxidation rate and thus the thickness of the resulting oxide layer being dependent on the light intensity at the surface of the semiconductor wafer, and

c) removal of the oxide layer,
the light intensity in step b) being predefined in a position-dependent manner in such a way that the differences in the position-dependent values of the parameter measured in step a) are reduced by the position-dependent oxidation rate resulting from the position-dependent light intensity in step b) and the subsequent removal of the oxide layer in step c).

The invention also relates to an apparatus for carrying out the method according to the invention.

Fig. 1